



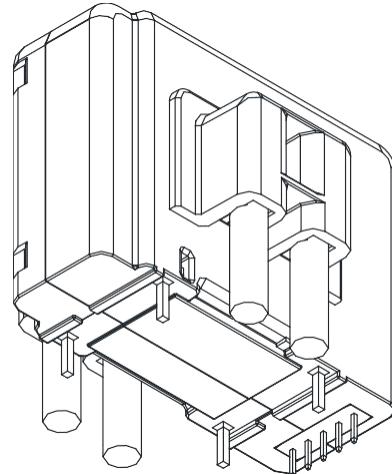
HS66-A-PB Series current sensor

Function description:

This series of sensors is based on Hall technology and closed-loop principle. It is suitable for measuring irregular current under DC, AC, pulse and various isolation conditions.

◆ Features:

- ◆ Closed-loop principle
- ◆ Voltage type output
- ◆ Single power supply
- ◆ Low temperature bleaching
- ◆ Strong anti-interference ability
- ◆ Wide measuring range



◆ Application field:

- ◆ AC variable speed and servo motor drive
- ◆ Battery power application
- ◆ Uninterruptible power supply (UPS)
- ◆ Switching Power Supply (SMPS)
- ◆ Welding power supply application
- ◆ Photovoltaic inverter

Model list:

Model number	Rated input current I_{PN} (A)	Measuring range I_{PM} (A)
HS66-100A-PB	100	± 270
HS66-150A-PB	150	± 450
HS66-200A-PB	200	± 450



TransFar

Beijing transfar electronics group co.,ltd

HS66-A-P series current sensor

HS66-100A-PB Parameter list

argument	symbol	unit	Minimum value	Typical value	Maximum value	remark
Electrical parameter						
Primary side rated current	I _{PN}	A		100		
Primary current measurement range	I _{PM}	A		±270		
Supply voltage	V _C	V	4.75	5	5.25	
Output voltage	V _{OUT}	V	V _{OUT} =G _{th} x I _P			@V _C =5V, @V _{OUT} to V _{REF}
Zero output voltage	V _{QOV}	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Reference voltage	V _{RE} F	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Electrical bias voltage (@IP=0)	V _{OE}	mV	-2.5	-	2.5	V _{OUT} -V _{REF}
Theoretical gain	G _{th}	mV/A	6.25			
Current consumption	I _C	mA		18 + I _p /N _s *1000	20+ I _p /N _s *1000	N _s =1300 turns
Magnetic bias current	I _{OM}	mA	-104	-	104	
Rated output @IPN	V _{FS}	V		0.625		V _{OUT} -V _{REF}
Performance parameter						
Nonlinear error	ε _L	%of I _{PN}	-0.15	-	0.15	@Zero error is not included V _{OE}
Gain error	ε _S	%of I _{PN}	-0.65	-	0.65	
Gain error temperature coefficient	TCS	ppm/K		-	70	ppm/K of I _{PN}
Total error at normal temperature	ε _{tot}	%of I _{PN}	-	-	0.95	
Total error @85 °C	ε _{tot}	%of I _{PN}	-	-	1.25	
Reference voltage temperature coefficient	TCU _{REF}	ppm/K	-100	-	100	
Response time	t _r	μS	-	-	3	
Band width	BW	kHz	200	-	-	@±3dB
Universal parameter						
Operating ambient temperature	T _A	°C	-40....+105			
Storage ambient temperature	T _S	°C	-55....+125			



TransFar

Beijing transfar electronics group co.,ltd

HS66-A-P series current sensor

HS66-150A-PB Parameter list

argument	symbol	unit	Minimum value	Typical value	Maximum value	remark
Electrical parameter						
Primary side rated current	I _{PN}	A		150		
Primary current measurement range	I _{PM}	A		±450		
Supply voltage	V _C	V	4.75	5	5.25	
Output voltage	V _{OUT}	V	V _{OUT} =G _{th} x I _P			@V _C =5V, @V _{OUT} to V _{REF}
Zero output voltage	V _{QOV}	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Reference voltage	V _{REF}	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Electrical bias voltage (@IP=0)	V _{OE}	mV	-2.5	-	2.5	V _{OUT} -V _{REF}
Theoretical gain	G _{th}	mV/A	4.166			
Current consumption	I _C	mA		18 + I _p /N _s *1000	20 + I _p /N _s *1000	N _s =1300 turns
Magnetic bias current	I _{OM}	mA	-156	-	156	
Rated output @IPN	V _{FS}	V		0.625		V _{OUT} -V _{REF}
Performance parameter						
Nonlinear error	ε _L	%of I _{PN}	-0.15	-	0.15	@Zero error is not included V _{OE}
Gain error	ε _S	%of I _{PN}	-0.65	-	0.65	
Gain error temperature coefficient	TCS	ppm/K		-	70	ppm/K of I _{PN}
Total error at normal temperature	ε _{tot}	%of I _{PN}	-	-	0.95	
Total error @85 °C	ε _{tot}	%of I _{PN}	-	-	1.25	
Reference voltage temperature coefficient	TCU _{REF}	ppm/K	-100	-	100	
Response time	t _r	μS	-	-	3	
Band width	BW	kHz	200	-	-	@±3dB
Universal parameter						
Operating ambient temperature	T _A	°C	-40....+105			
Storage ambient temperature	T _S	°C	-55....+125			



TransFar

Beijing transfar electronics group co.,ltd

HS66-A-P series current sensor

HS66-200A-PB Parameter list

argument	symbol	unit	Minimum value	Typical value	Maximum value	remark
Electrical parameter						
Primary side rated current	I _{PN}	A		200		
Primary current measurement range	I _{PM}	A		±450		
Supply voltage	V _C	V	4.75	5	5.25	
Output voltage	V _{OUT}	V	V _{OUT} =G _{th} x I _P			@V _C =5V, @V _{OUT} to V _{REF}
Zero output voltage	V _{QOV}	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Reference voltage	V _{RE} F	V	2.48	2.5	2.52	@V _C =5V, I _p =0A
Electrical bias voltage (@IP=0)	V _{OE}	mV	-2.5	-	2.5	V _{OUT} -V _{REF}
Theoretical gain	G _{th}	mV/A	3.125			
Current consumption	I _C	mA		18 + I _p /N _s *1000	20 + I _p /N _s *1000	N _s =1300 turns
Magnetic bias current	I _{OM}	mA	-208	-	208	
Rated output @IPN	V _{FS}	V		0.625		V _{OUT} -V _{REF}
Performance parameter						
Nonlinear error	ε _L	%of I _{PN}	-0.18	-	0.18	@不包含零点误差V _{OE}
Gain error	ε _S	%of I _{PN}	-0.65	-	0.65	
Gain error temperature coefficient	TCS	ppm/K		-	70	ppm/K of I _{PN}
Total error at normal temperature	ε _{tot}	%of I _{PN}	-	-	1.1	
Total error @85 °C	ε _{tot}	%of I _{PN}	-	-	1.4	
Reference voltage temperature coefficient	TCU _{REF}	ppm/K	-100	-	100	
Response time	t _r	μS	-	-	3	
Band width	BW	kHz	200	-	-	@±3dB
Universal parameter						
Operating ambient temperature	T _A	°C	-40....+105			
Storage ambient temperature	T _S	°C	-55....+125			



TransFar

Beijing transfar electronics group co.,ltd

HS66-A-P series current sensor

Attention:

- (1) Output voltage VOUT, zero output voltage VQOV, theoretical gain Gth and power supply VC are disproportionately dependent;
- (2) The frequency of the current to be measured should be limited to the sensor frequency band, otherwise it will cause overheating of the magnetic core and chip;
- (3) The wrong wiring method may damage the sensor;

Insulation characteristic:

argument	symbol	unit	Numerical value	remark
Ac isolation withstand voltage test RMS @ 50Hz,1min	U _D	KV	3	
Impulse withstand voltage	U _{NI}	KV	8	
Creepage distance	d _{CP}	mm	12.9	
Electrical clearance	d _{CI}	mm	12.9	
Relative marking index	CTI	-	600	

Maximum limit:

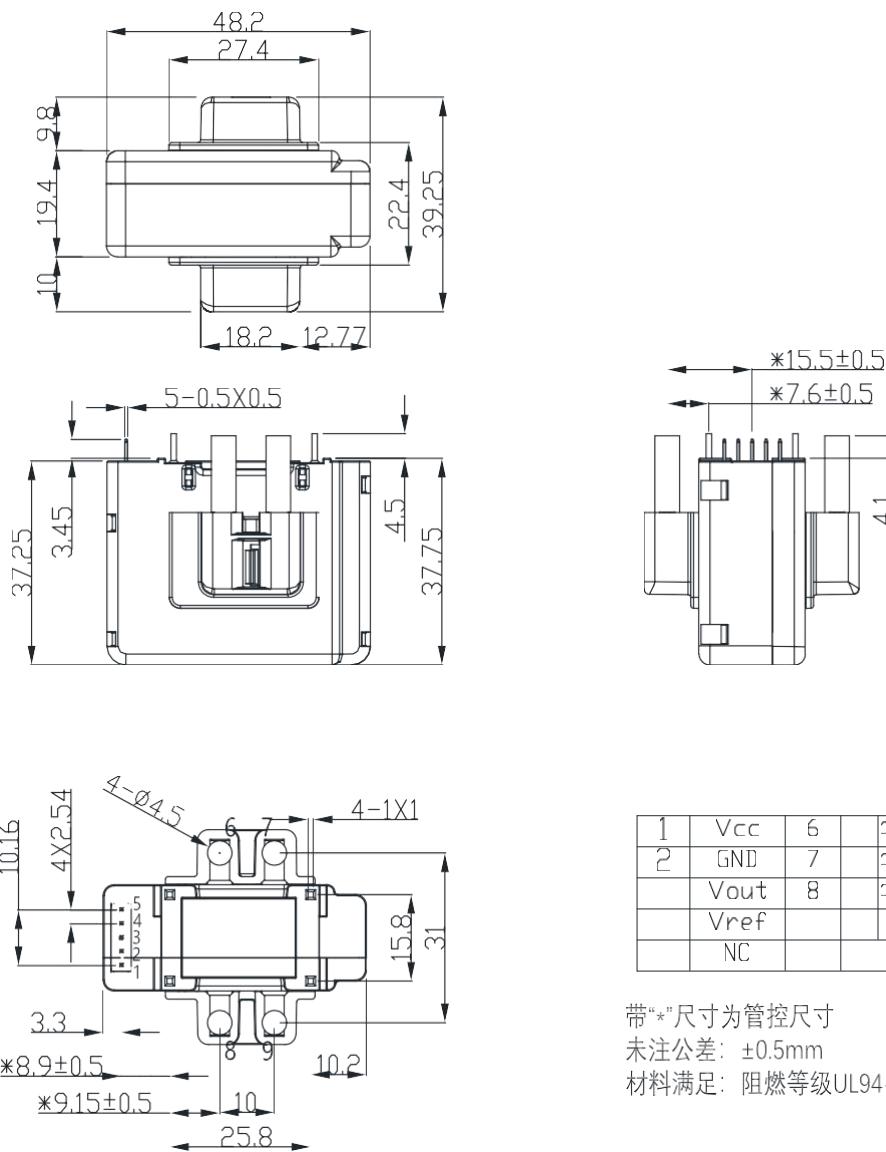
argument	symbol	unit	Numerical value	
Supply voltage	V _{Cmax}	V	7	
Maximum primary conductor temperature	T _{Bmax}	°C	110	
Maximum primary current	I _{Pmax}	A	10×I _{PN}	
Electrostatic discharge voltage (HBM - Human body model)	U _{ESD} HBM	kV	4	



TransFar®

Beijing transfar electronics group co.,ltd

HS66-A-P series current sensor

Machine size: (unit:mm)

1	Vcc	6	9+
2	GND	7	9+
	Vout	8	9-
	Vref		
	NC		

带“*”尺寸为管控尺寸

未注公差: ±0.5mm

材料满足: 阻燃等级UL94-VO, 符合RoHS

Attention:

Sensors must comply with IEC61010-1 standards. Sensors must be installed in electronic or electrical equipment that meets application standards and safety requirements in accordance with the instructions for use.

Watch out. Watch out for shocks.



When the sensor is working, some parts may be subjected to dangerous voltages (such as the primary busbar, power supply), and ignoring these will result in damage and serious danger. The sensor is a built-in device, and its conductive part must be guaranteed not to be touched by the outside world after installation. Protective case or shielding cover can be added if necessary. The main power supply must be able to be disconnected